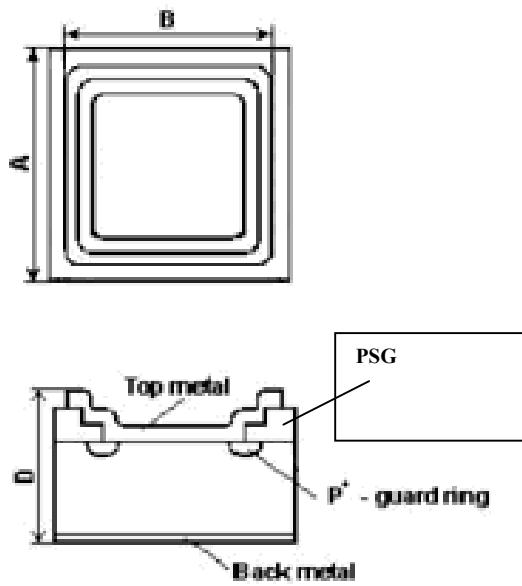


**SCHOTTKY DIODES. KDS-10040R.**  
PRELIMINARY.



Nov. 2011.

VSP-MIKRON	10A/40V. Die Size-115mil.			
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_B$	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ $25^\circ\text{C}$ , $I_F=10,0\text{A}$	$V_F$	V	0,40	0,38
Maximum Reverse Current @ $25^\circ\text{C}$ , $V_R=45\text{V}$ $25^\circ\text{C}$ , $V_R=40\text{V}$ $100^\circ\text{C}$ , $V_R=40\text{V}$	$I_R$	MA	- 3,5 3,5 120,0	3,5 2,5 100,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	200	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$ , $f=1\text{kHz.}$ , $T_J<150^\circ\text{C.}$	$I_{RRM}$	A	4,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	$\pm 8$ (contact)	
Voltage Rate of Change	$dV/dt$	V/ $\mu\text{S}$	10.000	
Operating Junction Temperature	$T_J$	°C	125	



DIM	ITEM	$\mu\text{m}$
$A_x$	Die Size	2920
$A_y$		2920
$B_x$	Top Metal Size	2780
$B_y$		2780
D	Thickness	300max.
	Scribe line Width	60

*Top metal:* a) Al – for Wire Bonding;  
b) Al-Ni-Ag – for Soldering.  
*Backside metal:* Ti-Ni-Ag.